

IRF9510 Datasheet

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DiGi Electronics Part Number	IRF9510-DG
Manufacturer	Vishay Siliconix
Manufacturer Product Number	IRF9510
Description	MOSFET P-CH 100V 4A TO220AB
Detailed Description	P-Channel 100 V 4A (Tc) 43W (Tc) Through Hole TO-220AB



Tel: +00 852-30501935

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Purchase and inquiry

Manufacturer Product Number:

IRF9510

Series:

-

FET Type:

P-Channel

Drain to Source Voltage (Vdss):

100 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

4V @ 250 μ A

Vgs (Max):

\pm 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

TO-220AB

Base Product Number:

IRF9510

Manufacturer:

Vishay Siliconix

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

4A (Tc)

Rds On (Max) @ Id, Vgs:

1.2Ohm @ 2.4A, 10V

Gate Charge (Qg) (Max) @ Vgs:

8.7 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

200 pF @ 25 V

Power Dissipation (Max):

43W (Tc)

Mounting Type:

Through Hole

Package / Case:

TO-220-3

Environmental & Export classification

RoHS Status:

RoHS non-compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

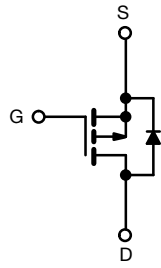
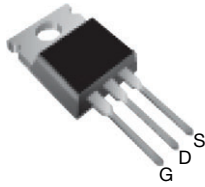
ECCN:

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Power MOSFET

TO-220AB



P-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- P-channel
- 175 °C operating temperature
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



Available
RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

PRODUCT SUMMARY

V_{DS} (V)	-100	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V	1.2
Q_g max. (nC)	8.7	
Q_{gs} (nC)	2.2	
Q_{gd} (nC)	4.1	
Configuration	Single	

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF9510PbF
Lead (Pb)-free and halogen-free	IRF9510PbF-BE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

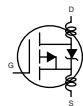
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	-100	V	
Gate-source voltage	V_{GS}	± 20		
Continuous drain current	V_{GS} at 10 V	$T_C = 25$ °C	-4.0	A
		$T_C = 100$ °C	-2.8	
Pulsed drain current ^a	I_{DM}	-16		
Linear derating factor		0.29	W/°C	
Single pulse avalanche energy ^b	E_{AS}	200	mJ	
Repetitive avalanche current ^a	I_{AR}	-4.0	A	
Repetitive avalanche energy ^a	E_{AR}	4.3	mJ	
Maximum power dissipation	$T_C = 25$ °C	P_D	43	W
Peak diode recovery dV/dt ^c	dV/dt	-5.5	V/ns	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^d	For 10 s	300		
Mounting torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = -25$ V, starting $T_J = 25$ °C, $L = 18$ mH, $R_g = 25$ Ω , $I_{AS} = -4.0$ A (see fig. 12)
- $I_{SD} \leq -4.0$ A, $dI/dt \leq 75$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C
- 1.6 mm from case



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	3.5	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	-100	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$	-	-0.091	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -100\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	-100	μA
		$V_{DS} = -80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$	-	-	-500	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -2.4\text{ A}^b$	-	-	1.2	Ω
Forward transconductance	g_{fs}	$V_{DS} = -50\text{ V}$, $I_D = -2.4\text{ A}^b$	1.0	-	-	S
Dynamic						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	200	-	μF
Output capacitance	C_{oss}		-	94	-	
Reverse transfer capacitance	C_{rss}		-	18	-	
Total gate charge	Q_g	$V_{GS} = -10\text{ V}$, $I_D = -4.0\text{ A}$, $V_{DS} = -80\text{ V}$, see fig. 6 and 13 ^b	-	-	8.7	nC
Gate-source charge	Q_{gs}		-	-	2.2	
Gate-drain charge	Q_{gd}		-	-	4.1	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -50\text{ V}$, $I_D = -4.0\text{ A}$, $R_g = 24\text{ }\Omega$, $R_D = 11\text{ }\Omega$, see fig. 10 ^b	-	10	-	ns
Rise time	t_r		-	27	-	
Turn-off delay time	$t_{d(off)}$		-	15	-	
Fall time	t_f		-	17	-	
Gate input resistance	R_g	$f = 1\text{ MHz}$, open drain	1.5	-	7.9	Ω
Internal drain inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact	-	4.5	-	nH
Internal source inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode	-	-	-4.0	A
Pulsed diode forward current ^a	I_{SM}		-	-	-16	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = -4.0\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	-5.5	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = -4.0\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	82	160	ns
Body diode reverse recovery charge	Q_{rr}		-	0.15	0.30	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

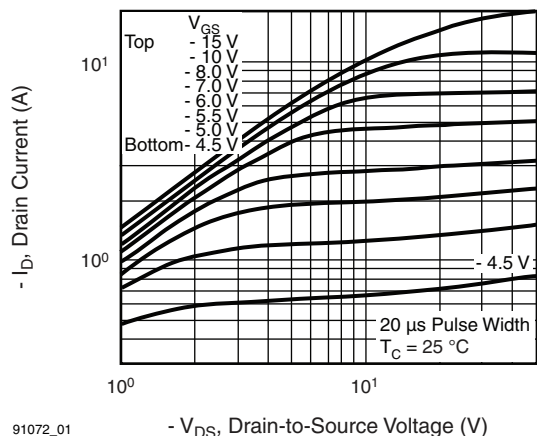


Fig. 1 - Typical Output Characteristics, TC = 25 °C

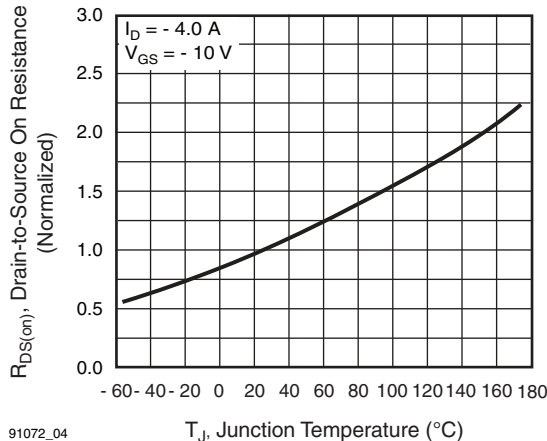


Fig. 4 - Normalized On-Resistance vs. Temperature

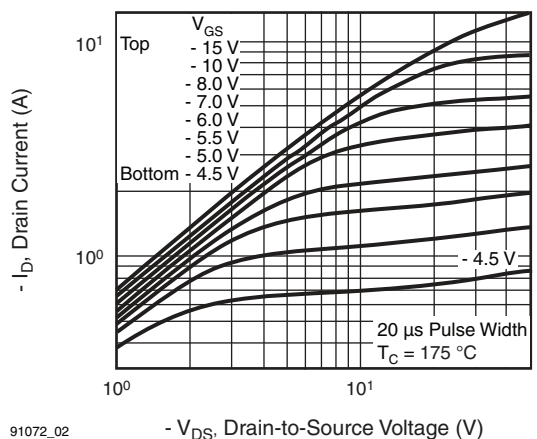


Fig. 2 - Typical Output Characteristics, TC = 175 °C

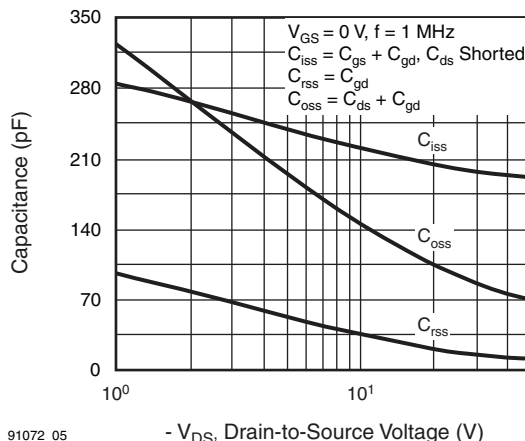


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

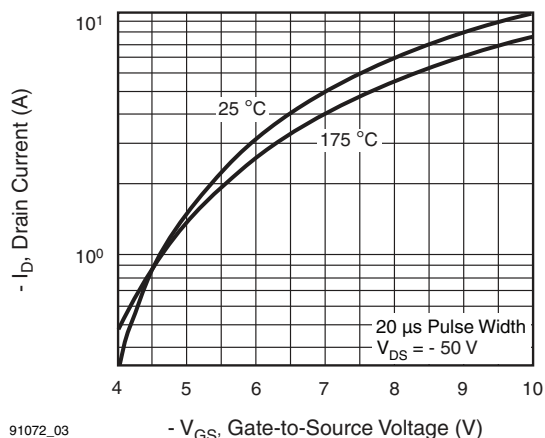


Fig. 3 - Typical Transfer Characteristics

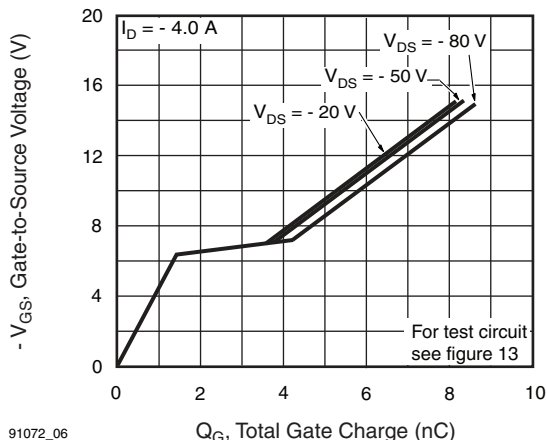
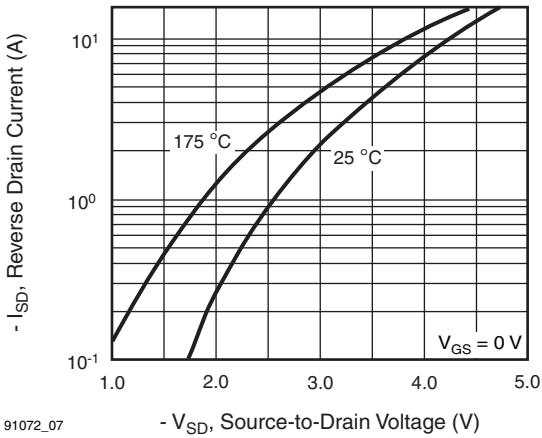
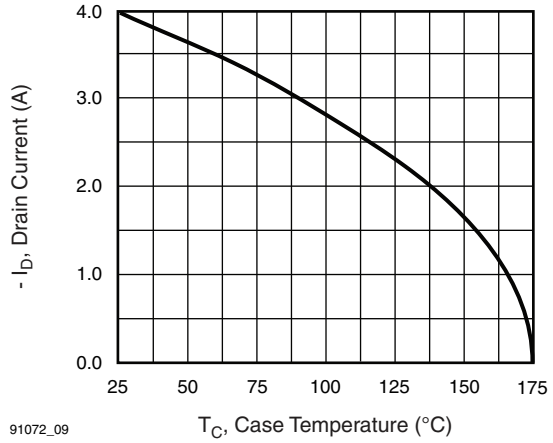


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



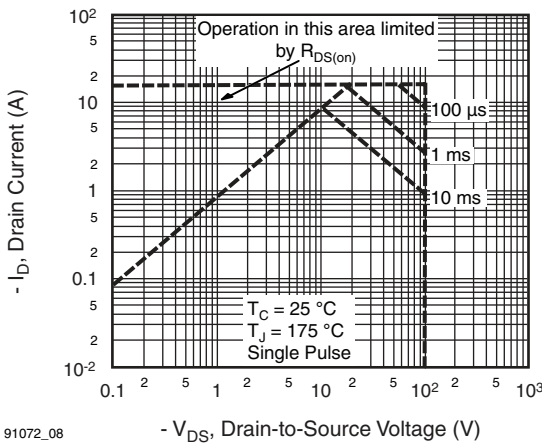
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 9 - Maximum Drain Current vs. Case Temperature



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Fig. 8 - Maximum Safe Operating Area

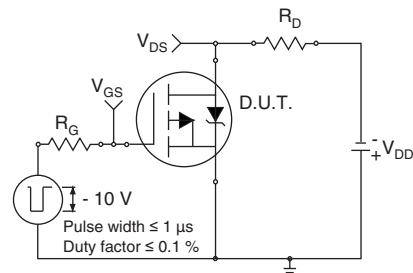


Fig. 10a - Switching Time Test Circuit

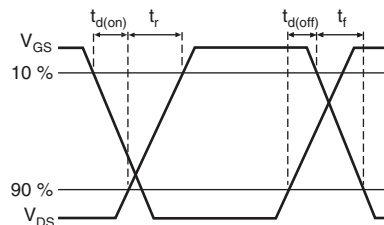
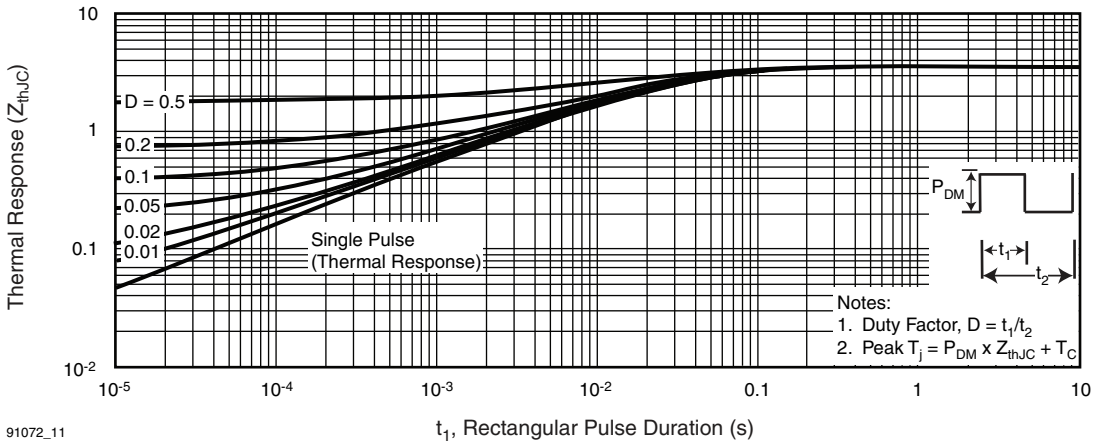


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

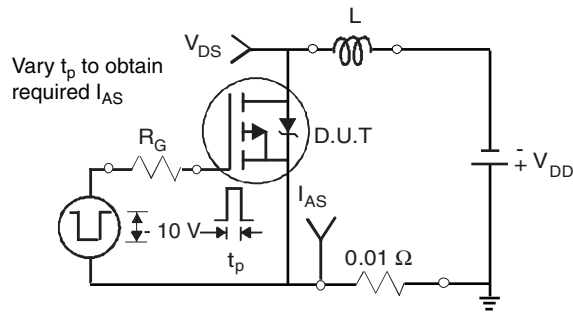


Fig. 12a - Unclamped Inductive Test Circuit

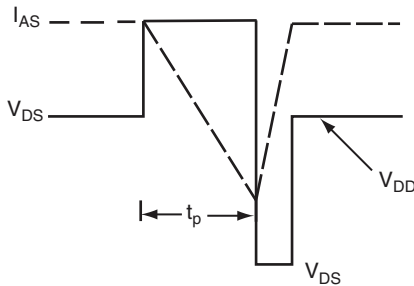
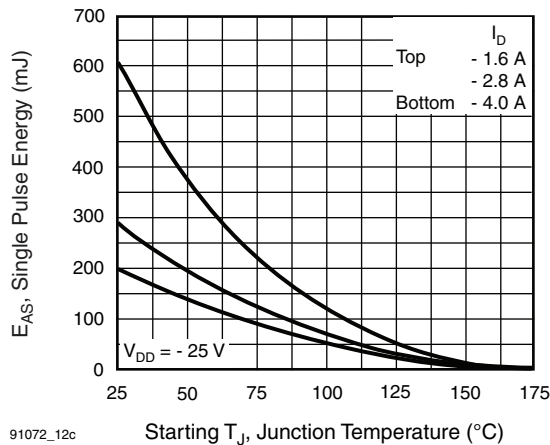


Fig. 12b - Unclamped Inductive Waveforms



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Fig. 12 c- Maximum Avalanche Energy vs. Drain Current

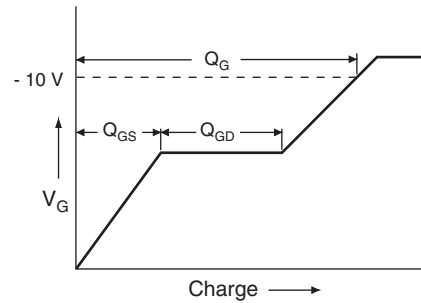


Fig. 13a - Basic Gate Charge Waveform

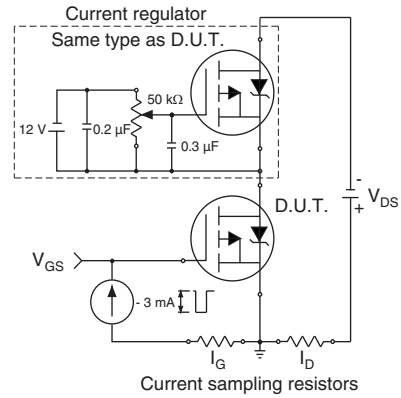
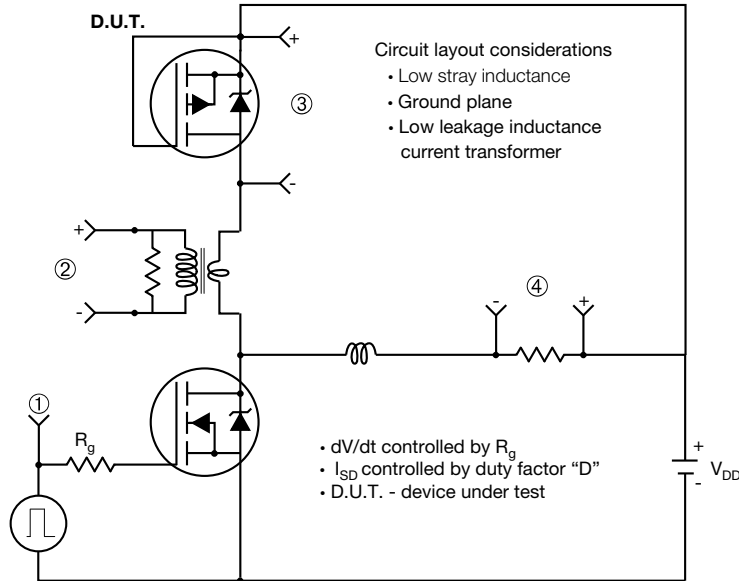


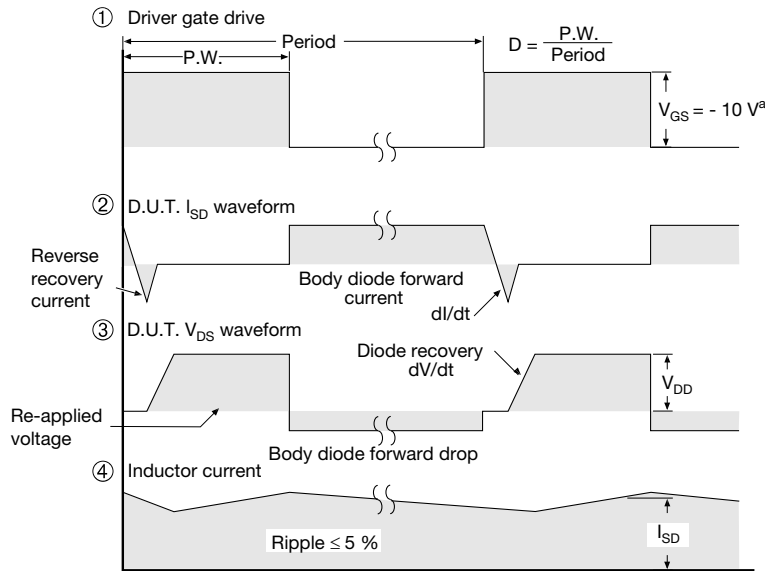
Fig. 13b - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



Note
 • Compliment N-Channel of D.U.T. for driver



Note
 a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 14 - For P-Channel

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